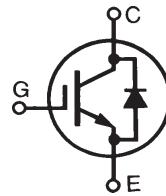


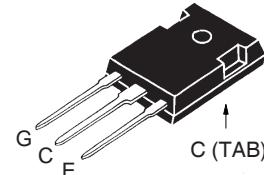
PolarHV™ IGBT**IXGH28N60B3D1**

V_{CES} = 600V
I_{C110} = 28A
V_{CE(sat)} ≤ 1.8V

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	T _J = 25°C to 150°C	600	V
V_{CGR}	T _J = 25°C to 150°C, R _{GE} = 1MΩ	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	T _C = 25°C	66	A
I_{C110}	T _C = 110°C	28	A
I_{F110}	T _C = 110°C	10	A
I_{CM}	T _C = 25°C, 1ms	150	A
SSOA (RBSOA)	V _{GE} = 15V, T _{VJ} = 125°C, R _G = 10Ω Clamped inductive load @ ≤ 600V	I _{CM} = 60	A
P_c	T _C = 25°C	190	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	1.6mm (0.062 in.) from case for 10 seconds	300	°C
T_{SOLD}	Plastic body for 10 seconds	260	°C
M_d	Mounting torque (M3)	1.13/10	Nm/lb.in.
Weight		6	g

Symbol	Test Conditions (T _J = 25°C unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	I _C = 250μA, V _{GE} = 0V	600		V
V_{GE(th)}	I _C = 250μA, V _{CE} = V _{GE}	3.0	5.0	V
I_{CES}	V _{CE} = V _{CES} , V _{GE} = 0V T _J = 125°C		50 1.0	μA mA
I_{GES}	V _{CE} = 0V, V _{GE} = ± 20V		±100	nA
V_{CE(sat)}	I _C = 24A, V _{GE} = 15V, Note 1	1.5	1.8	V

TO-247 (IXGH)



G = Gate C = Collector
 E = Emitter TAB = Collector

Features

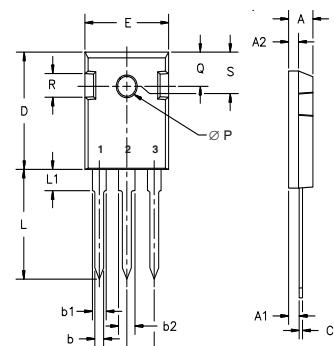
- Square RBSOA
- High current handling capability
- MOS Gate turn-on
 - drive simplicity

Applications

- PFC circuits
- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies
- AC motor speed control
- DC servo and robot drives
- DC choppers

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = I_{C110}$, $V_{CE} = 10\text{V}$, Note 1	18	30	S
C_{ies} C_{oes} C_{res}	$V_{CE} = 25\text{V}$, $V_{GE} = 0\text{V}$, $f = 1\text{MHz}$	2320	pF	
		176	pF	
		24	pF	
Q_g Q_{ge} Q_{gc}	$I_C = I_{C110}$, $V_{GE} = 15\text{V}$, $V_{CE} = 0.5 \cdot V_{CES}$	62	nC	
		11	nC	
		23	nC	
$t_{d(on)}$ t_{ri} E_{on} $t_{d(off)}$ t_{fi} E_{off}	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 24\text{A}$, $V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}$, $R_G = 10\Omega$	19	ns	
		24	ns	
		0.34	mJ	
		125	200	ns
		100	160	ns
		0.65	1.2	mJ
$t_{d(on)}$ t_{ri} E_{on} $t_{d(off)}$ t_{fi} E_{off}	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = 24\text{A}$, $V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}$, $R_G = 10\Omega$	19	ns	
		26	ns	
		0.6	mJ	
		180	ns	
		170	ns	
		1.0	mJ	
R_{thJC}			0.66	°C/W
R_{thCS}		0.21		°C/W

TO-247 (IXGH) Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC

Reverse Diode (FRED)

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
V_F	$I_F = 24\text{A}$, $V_{GE} = 0\text{V}$, Note 1		2.5	V
	$T_J = 150^\circ\text{C}$		1.7	V
I_{RM}	$I_F = 24\text{A}$, $V_{GE} = 0\text{V}$, $-di_F/dt = 100\text{A}/\mu\text{s}$	5		A
t_{rr}	$V_R = 100\text{V}$			
	$I_F = 1\text{A}$, $-di_F/dt = 100\text{A}/\mu\text{s}$, $V_R = 30\text{V}$	25	ns	
	$T_J = 100^\circ\text{C}$	100	ns	
R_{thJC}			1.0	K/W

Note 1: Pulse test, $t \leq 300\mu\text{s}$; duty cycle, $d \leq 2\%$.

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

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